Electronic Supplementary Information

Gigantic work function in layered AgF₂

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S1. Computational methodology and determination of workfunction:

Projector-augmented-wave (PAW) method was applied^[1,2] with rotationally invariant LSDA+U approach introduced by Liechtenstein *et al.*^[3]. U and J values for Ag were set to be 5 eV and 1 eV, respectively, as it was previously applied for bulk AgF₂ ^[4,5]. Vienna Ab initio simulation package, VASP 5.4.1, was used for all computations^[6–9].

AgF₂ bulk: Cut-off energy for plane wave basis set was set to $E_{cut} = 520$ eV. The blocked Davidson iteration scheme was used. Force, stress tensor, ions, cell shape and cell volume were relaxed. The energy convergence criterion (SCF) was set to 1 x 10⁻⁷ eV. The relaxations were stopped if all forces were smaller than 0.0003 eV/Å. Interpolation formula according to Vosko, Wilk and Nusair was used^[10]. Gaussian smearing was used while ionic relaxation with conjugate gradient algorithm were performed. Tetrahedron method with Blöchl corrections were used for no update option. Smearing width was set to 0.04 eV. The k-point mesh of 12x12x12 was used for the magnetic cell identical with unit cell. The optimized lattice parameters of *P*bca cell 5.499 Å, 5.826 Å, and 5.056 Å match well the experimental values of 5.529 Å, 5.813 Å and 5.073 Å, respectively^[11], discrepancies not exceeding 0.6%. Figure S2 shows calculated DOS for bulk system.

Unoptimized AgF₂ N-layer systems from the bulk: In order to calculate work function of AgF₂, N=1, 3, 5, 7, 9, 11 surface systems were constructed from preoptimized bulk AgF₂ with their geometry constrained to that found in a crystal. Unit cell were multiplied in the direction perpendicular to the layers to obtain the desired number of layers for further modelling, and to expose the (010) surface sheet towards the vacuum. Such choice of the surface is most natural since the inter-sheet interactions are weak leading to facile cleavage of the layers. *Ca.* 22.5 Å vacuum slab was added to obtained slabs (*cf.* SI for exemplary structure, Figure S1). Single point energies were calculated, followed by the density of states (with DOS evaluation at 3000 grid points) and the total local potential calculations. k-mesh in direction of added vacuum was reduced accordingly to preserve mesh density, with remaining parameters unchanged as compared to the bulk system. Exemplary DOS for N=9 system is showed at Figure S3.

Optimization of AgF_2 N=1 layer system: Geometry of the N = 1 AgF_2 layer system was optimized. The system was created by first cutting off the middle AgF_2 layer from the bulk structure. To prevent the collapse of the vacuum slab during optimization, the void was filled by adding helium atoms in the fractional $(0, \frac{1}{2}, 0)$ and $(\frac{1}{2}, \frac{1}{2}, \frac{1}{2})$ sites. The distance between helium atoms was sufficiently large (over twice their van der Waals radius) to prevent their repulsion; in this way, small atoms of totally inert noble gas served as separator, which does not influence the crystal structure. After optimization, helium atoms were removed, and a vacuum slab was increased to ~12.5 Å while preserving the geometry of the AgF_2 single layer, and angles between unit cell vectors. So constructed system was used for calculation of the work function.

Optimization of hypothetical AgF₂ N=1 flat layer system: Geometry of the N = 1 hypothetical AgF₂ flat layer system was optimized. The preliminary structure model was similar to the one described above, albeit it was forced to be tetragonal, with F atoms placed in ($\frac{1}{2}00$) and ($\frac{00}{2}$) positions. Similarly, to prevent the collapse of the vacuum slab during optimization, the void was filled by adding helium atoms in the fractional ($0,\frac{1}{2},0$) and ($\frac{1}{2},\frac{1}{2},\frac{1}{2}$) sites. After optimization, helium atoms were removed, and a vacuum slab was increased to ~12.5 Å while preserving the geometry of the AgF₂ single flat layer.

AgF reference system:

Bulk AgF was optimized using DFT without spin polarization. The optimized lattice parameter of 4.88 Å matches the experimental value of 4.92 Å^[12], discrepancy not exceeding *c.a.* 0.8%. After that N-layered systems for N=1,3, 5, 7, 9, 11 and exposing the (100) surface, were created using preoptimized bulk, and calculations with frozen geometries were performed. AgF slabs were separated with a vacuum one of *ca.* 22.5 Å.

Ag₂F reference system:

Bulk Ag₂F was optimized in the analogous manner as AgF. The optimized lattice parameter of a=b=2.945 Å and c=5.727 Å matches the experimental value of a=b=2.999 and c=5.695 Å, discrepancy not exceeding 1.8% and 0.5%, respectively. After that N-layered systems for N=1, 3, 5, 7, 9, 11 and exposing the (001) surface (F terminals) were created in an analogous manner as for AgF, using preoptimized bulk, and calculations with frozen geometries were performed. Ag₂F Slabs were separated with a vacuum slab of *ca.* 22.5 Å.

Evaluation of work function:

The minimum work needed to remove one electron from an oriented slab occupied states to a remote point in vacuum is characterised by work function (W) defined by the difference^[13]:

$$W = E_{vacuum} - E_F \qquad (Eq. 1),$$

where (E_{vacuum}) is electrostatic potential in vacuum near surface as obtained from a maximum of planar averaged local electrostatic potential in supercell vacuum space between slab mirrors (determined using the VASP and P4VASP tool^[14], and (E_F) is the Fermi level of the slab.

P4VASP and VESTA programs were used for drawings in this work^[14,15]

S2. Reference system: N-surface NaF systems slabs from optimized bulk material:

Bulk NaF was optimized with the same parameters as for bulk AgF_2 , using DFT without spin polarization. The optimized lattice parameter of 4.628 Å matches the experimental value of 4.619 Å^[16], discrepancy not exceeding 0.2%. After that N-layered systems for N=3, 5, 7, 9, 11 and exposing the (100) surface were created in an analogous manner as for AgF_2 , using preoptimized bulk, and calculations with frozen geometries were performed. Slabs were separated with a vacuum slab of *ca.* 24.5 Å. The same set of calculations were conducted for N-layered NaF systems as previously for unoptimized AgF_2 N-layered ones.

In Table S1 values obtained for NaF reference system are summarized. Here we see that with increasing thickness of the slab (N) values of E_{vacuum} and E_F are increasing. Work Function is rather stable and not dependent on slab thickness, and its value can be approximated to 6.7 eV.

		N	N	BG	[eV]	Evad	cuum	E	F	W	
		3	;	5.6	648	1.0	90	-5.5	580	6.671	
		5	5	5.7	'19	1.5	60	-5.1	21	6.681	
		7	7	5.7	45	1.9	17	-4.7	766	6.683	
		9)	5.7	61	2.1	98	-4.4	183	6.681	
		1	1	5.7	62	2.4	24	-4.2	262	6.686	
bulk	5.5	553	-		-1.	993					

Table S1. Results obtained from DFT calculation for not optimized N-layered systems of NaF build from optimized bulk material: Band Gap (BG), Vacuum energy (E_{vacuum}), Fermi Energy (E_F) and Work Function (W).



S3. Reference system: N-surface AgF systems slabs from optimized bulk material:



Figure S2. Work function for AgF.

				N	E _{vacuum}	E _F	W
				1	0.855	-4.396	5.251
				3	2.136	-3.048	5.184
				5	3.059	-2.185	5.244
				7	3.742	-1.469	5.212
				9	4.287	-0.941	5.228
11	4.719	-0.505	5	.224			

 Table S2. Results obtained from DFT calculation for not optimized N-layered systems of AgF build from optimized bulk

 material: Vacuum energy (E_{vacuum}), Fermi Energy (E_F) and Work Function (W).



S4. Reference system: N-surface Ag₂F systems slabs from optimized bulk material:

Table S3. Results obtained from DFT calculation for not optimized N-layered systems of NaF build from optimized bulk material: Band Gap (BG), Vacuum energy (E_{vacuum}), Fermi Energy (E_F) and Work Function (W).

Ν	E _{vacuum}	E _F	W
1	2.093	-3.147	5.240
3	4.639	-0.602	5.242
5	6.121	0.880	5.241
7	7.087	1.846	5.241
9	7.768	2.526	5.242

S5. Full DOS for relevant AgF₂ systems.



Full DOS is shown here to supplement information about the most relevant regions provided in the main text. One may easily notice that the absolute values of DOS are the largest for flat AgF₂ in several energy regions; this stems from the weakest mutual interactions of the Ag d(z^2) orbitals which concomitantly result in a narrow band and high local DOS. Similar argument applies to the F p(z) orbitals. On the other hand, the orthogonal orbitals such as Ag (x^2 - y^2) or F p(x)/p(y) now interact most strongly among the three systems presented, which leads to substantial band dispersion and the smallest local DOS in the LHB & UHB, as discussed in the manuscript.

S6. Magnetic superexchange constant, J, in bulk AgF₂ and N=1 optimized system.

Magnetic superexchange in optimized single-layer as compared to bulk AgF_2 has been rationalized using previously published model [S17]. The angular dependence of J originates from the said reference. Now, two theoretical points from the current work have been overlaid; the filled blue triangle corresponds to computed AgF_2 structure in the bulk, while the empty triangle stands for the parameters calculated for an optimized single layer of AgF_2 . It may be seen that both points fit the theoretical dependence quite well. This factor alone suffices to state that large differences between the calculated Ag-F-Ag angles in the bulk and in an optimized single layer of AgF_2 allows us to explain the observed dramatic nearly 10-fold differences of J between these two structures.

On the other hand, the computed value for the flat layer system (ca. -200 meV) departs somewhat from that predicted by the model (of ca. -250 meV). However, the published model [S17] is valid only if U, charge transfer Δ , nearest neighbor repulsion, etc. remain the same. Since the flat layer form is characterized by the lack of apical fluorine, very large change in Δ as well as nearest neighbor repulsion are expected as compared to the bulk. Thus, the -200 vs.-250 meV discrepancy may rather easily be justified.

S7. Crystallographic Information Files.

CIF file for bulk AgF₂ optimized system:

CRYSTAL DATA

#=

#-----

data_AgF2_Bulk

"
5.49911
5.82599
5.05574
90
90
90
alt 'P 1
1

loop_

_space_group_symop_operation_xyz 'x, y, z'

loop

· -									
atom	_site_la	abel							
_atom_site_occupancy									
_atom_site_fract_x									
atom	_atom_site_fract_y								
atom	_site_fi	ract_z							
atom	_site_a	dp_type							
_atom_site_B_iso_or_equiv									
atom	_site_ty	ype_symbol							
Ag1	1.0	0.000000	-0.000000	0.000000	Biso 1.000000 Ag				
Ag2	1.0	0.500000	0.000000	0.500000	Biso 1.000000 Ag				
Ag3	1.0	0.000000	0.500000	0.500000	Biso 1.000000 Ag				
Ag4	1.0	0.500000	0.500000	0.000000	Biso 1.000000 Ag				
F1	1.0	0.305732	0.868176	0.183685	Biso 1.000000 F				
F2	1.0	0.694268	0.131824	0.816315	Biso 1.000000 F				
F3	1.0	0.194268	0.131824	0.683685	Biso 1.000000 F				
F4	1.0	0.805732	0.868176	0.316315	Biso 1.000000 F				
F5	1.0	0.694268	0.368176	0.316315	Biso 1.000000 F				
F6	1.0	0.305732	0.631824	0.683685	Biso 1.000000 F				
F7	1.0	0.805732	0.631824	0.816315	Biso 1.000000 F				
F8	1.0	0.194268	0.368176	0.183685	Biso 1.000000 F				

CIF file for N=1 layer AgF₂ optimized system:

#========

CRYSTAL DATA

#-----

data_AgF2_1N

_chemical_name_common	"
_cell_length_a	5.72758
_cell_length_b	25.08496
_cell_length_c	3.72589
_cell_angle_alpha	90
_cell_angle_beta	90
_cell_angle_gamma	74.49773
_space_group_name_H-M_alt	'P 1'
_space_group_IT_number	1

loop_

_space_group_symop_operation_xyz 'x, y, z' loop _atom_site_label atom site occupancy atom site fract x _atom_site_fract y atom site fract z atom site adp type atom site B iso or equiv _atom_site_type_symbol Ag1 1.0 0.000000 0.125000 0.500000 Biso 1.000000 Ag 1.0 Ag2 0.500000 0.125000 0.000000 Biso 1.000000 Ag F1 1.0 0.728499 0.086095 Biso 1.000000 F 0.407047 F2 1.0 0.271501 0.163905 0.592953 Biso 1.000000 F F3 1.0 0.771501 0.907047 Biso 1.000000 F 0.163905 F4 1.0 0.092953 0.228499 0.086095 Biso 1.000000 F

CIF file for N=1 layer AgF₂ optimized tetragonal flat layer system:

CRYSTAL DATA

#-----

data_AgF2_1Nflat

_chemical_name_common	"
_cell_length_a	8.04142
_cell_length_b	25.58947
_cell_length_c	8.04037
_cell_angle_alpha	90
_cell_angle_beta	90
_cell_angle_gamma	90
_space_group_name_H-M_a	alt 'P 1'
_space_group_IT_number	1

loop_

_space_group_symop_operation_xyz 'x, y, z'

loop_

_atom_site_label _atom_site_occupancy _atom_site_fract_x _atom_site_fract_y _atom_site_fract_z _atom_site_adp_type _atom_site_B_iso_or_equiv _atom_site_type_symbol

Ag1	1.0	0.000000	0.109214	0.000000	Biso 1.000000 Ag
Ag2	1.0	0.000000	0.109214	0.500000	Biso 1.000000 Ag
Ag3	1.0	0.500000	0.109214	0.000000	Biso 1.000000 Ag
Ag4	1.0	0.500000	0.109214	0.500000	Biso 1.000000 Ag
F1	1.0	0.250000	0.109214	0.000000	Biso 1.000000 F
F2	1.0	0.250000	0.109214	0.500000	Biso 1.000000 F
F3	1.0	0.750000	0.109214	0.000000	Biso 1.000000 F
F4	1.0	0.750000	0.109214	0.500000	Biso 1.000000 F
F5	1.0	0.000000	0.109214	0.250000	Biso 1.000000 F
F6	1.0	0.000000	0.109214	0.750000	Biso 1.000000 F
F7	1.0	0.500000	0.109214	0.250000	Biso 1.000000 F
F8	1.0	0.500000	0.109214	0.750000	Biso 1.000000 F

CIF file for N=11 layer AgF₂ unoptimized system:

#-----

CRYSTAL DATA

#-----

data_AgF2_N11

_chemica	al_name	e_common	,	• •			
_cell_len	igth_a	_	5.49911				
_cell_len	igth_b		54.9559	6			
_cell_len	igth_c		5.05574				
_cell_ang	gle_alpl	na	90				
_cell_ang	gle_beta	a	90				
_cell_ang	gle_gan	nma	90				
_space_g	group_n	ame_H-M_al	t	'P 1	,		
_space_g	group_ľ	T_number	1				
loop_							
_space_g	group_s	ymop_operati	ion_xyz				
'x, y, z'							
loop_							
atom	_site_lal	pel					
atom	_site_oc	cupancy					
atom	_site_fra	act_x					
atom	_site_fra	act_y					
atom	_site_fra	ict_z					
_atom_site_adp_type							
atom	_site_B_	_iso_or_equiv	7				
atom	_site_ty	pe_symbol					
Ag1	1.0	0.000000	0.10601	2	0.000000	Biso	1.000000 Ag
Ag2	1.0	0.000000	0.21202	24	0.000000	Biso	1.000000 Ag
Ag3	1.0	0.000000	0.31803	6	0.000000	Biso	1.000000 Ag

Ag4	1.0	0.000000	0.424048	0.000000	Biso 1.000000 Ag
Ag5	1.0	0.000000	0.530060	0.000000	Biso 1.000000 Ag
Ag6	1.0	0.500000	0.106012	0.500000	Biso 1.000000 Ag
Ag7	1.0	0.500000	0.212024	0.500000	Biso 1.000000 Ag
Ag8	1.0	0.500000	0.318036	0.500000	Biso 1.000000 Ag
Ag9	1.0	0.500000	0.424048	0.500000	Biso 1.000000 Ag
Ag10	1.0	0.500000	0.530060	0.500000	Biso 1.000000 Ag
Ag11	1.0	0.000000	0.053006	0.500000	Biso 1.000000 Ag
Ag12	1.0	0.000000	0.159018	0.500000	Biso 1.000000 Ag
Ag13	1.0	0.000000	0.265030	0.500000	Biso 1.000000 Ag
Ag14	1.0	0.000000	0.371042	0.500000	Biso 1.000000 Ag
Ag15	1.0	0.000000	0.477054	0.500000	Biso 1.000000 Ag
Ag16	1.0	0.000000	0.583066	0.500000	Biso 1.000000 Ag
Ag17	1.0	0.500000	0.053006	0.000000	Biso 1.000000 Ag
Ag18	1.0	0.500000	0.159018	0.000000	Biso 1.000000 Ag
Ag19	1.0	0.500000	0.265030	0.000000	Biso 1.000000 Ag
Ag20	1.0	0.500000	0.371042	0.000000	Biso 1.000000 Ag
Ag21	1.0	0.500000	0.477054	0.000000	Biso 1.000000 Ag
Ag22	1.0	0.500000	0.583066	0.000000	Biso 1.000000 Ag
FĨ	1.0	0.305732	0.092037	0.183685	Biso 1.000000 F
F2	1.0	0.305732	0.198049	0.183685	Biso 1.000000 F
F3	1.0	0.305732	0.304061	0.183685	Biso 1.000000 F
F4	1.0	0.305732	0.410073	0.183685	Biso 1.000000 F
F5	1.0	0.305732	0.516085	0.183685	Biso 1.000000 F
F6	1.0	0.694268	0.119987	0.816315	Biso 1.000000 F
F7	1.0	0.694268	0.225999	0.816315	Biso 1.000000 F
F8	1.0	0.694268	0.332011	0.816315	Biso 1.000000 F
F9	1.0	0.694268	0.438023	0.816315	Biso 1.000000 F
F10	1.0	0.694268	0.544035	0.816315	Biso 1.000000 F
F11	1.0	0.194268	0.119987	0.683685	Biso 1.000000 F
F12	1.0	0.194268	0.225999	0.683685	Biso 1.000000 F
F13	1.0	0.194268	0.332011	0.683685	Biso 1.000000 F
F14	1.0	0.194268	0.438023	0.683685	Biso 1.000000 F
F15	1.0	0.194268	0.544035	0.683685	Biso 1.000000 F
F16	1.0	0.805732	0.092037	0.316315	Biso 1.000000 F
F17	1.0	0.805732	0.198049	0.316315	Biso 1.000000 F
F18	1.0	0.805732	0.304061	0.316315	Biso 1.000000 F
F19	1.0	0.805732	0.410073	0.316315	Biso 1.000000 F
F20	1.0	0.805732	0.516085	0.316315	Biso 1.000000 F
F21	1.0	0.694268	0.039031	0.316315	Biso 1.000000 F
F22	1.0	0.694268	0.145043	0.316315	Biso 1.000000 F
F23	1.0	0.694268	0.251055	0.316315	Biso 1.000000 F
F24	1.0	0.694268	0.357067	0.316315	Biso 1.000000 F
F25	1.0	0.694268	0.463079	0.316315	Biso 1.000000 F
F26	1.0	0.694268	0.569091	0.316315	Biso 1.000000 F
F27	1.0	0.305732	0.066981	0.683685	Biso 1.000000 F
F28	1.0	0.305732	0.172993	0.683685	Biso 1.000000 F
F29	1.0	0.305732	0.279005	0.683685	Biso 1.000000 F
F30	1.0	0.305732	0.385017	0.683685	Biso 1.000000 F
F31	1.0	0.305732	0.491029	0.683685	Biso 1.000000 F

F32	1.0	0.305732	0.597041	0.683685	Biso 1.000000 F
F33	1.0	0.805732	0.066981	0.816315	Biso 1.000000 F
F34	1.0	0.805732	0.172993	0.816315	Biso 1.000000 F
F35	1.0	0.805732	0.279005	0.816315	Biso 1.000000 F
F36	1.0	0.805732	0.385017	0.816315	Biso 1.000000 F
F37	1.0	0.805732	0.491029	0.816315	Biso 1.000000 F
F38	1.0	0.805732	0.597041	0.816315	Biso 1.000000 F
F39	1.0	0.194268	0.039031	0.183685	Biso 1.000000 F
F40	1.0	0.194268	0.145043	0.183685	Biso 1.000000 F
F41	1.0	0.194268	0.251055	0.183685	Biso 1.000000 F
F42	1.0	0.194268	0.357067	0.183685	Biso 1.000000 F
F43	1.0	0.194268	0.463079	0.183685	Biso 1.000000 F
F44	1.0	0.194268	0.569091	0.183685	Biso 1.000000 F

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